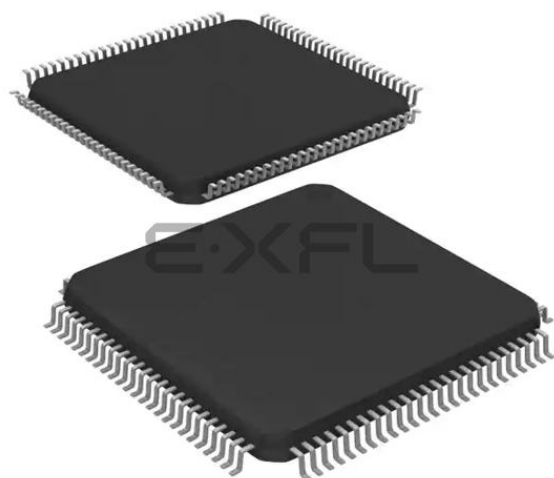




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Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	85
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg280f128-qfp100t

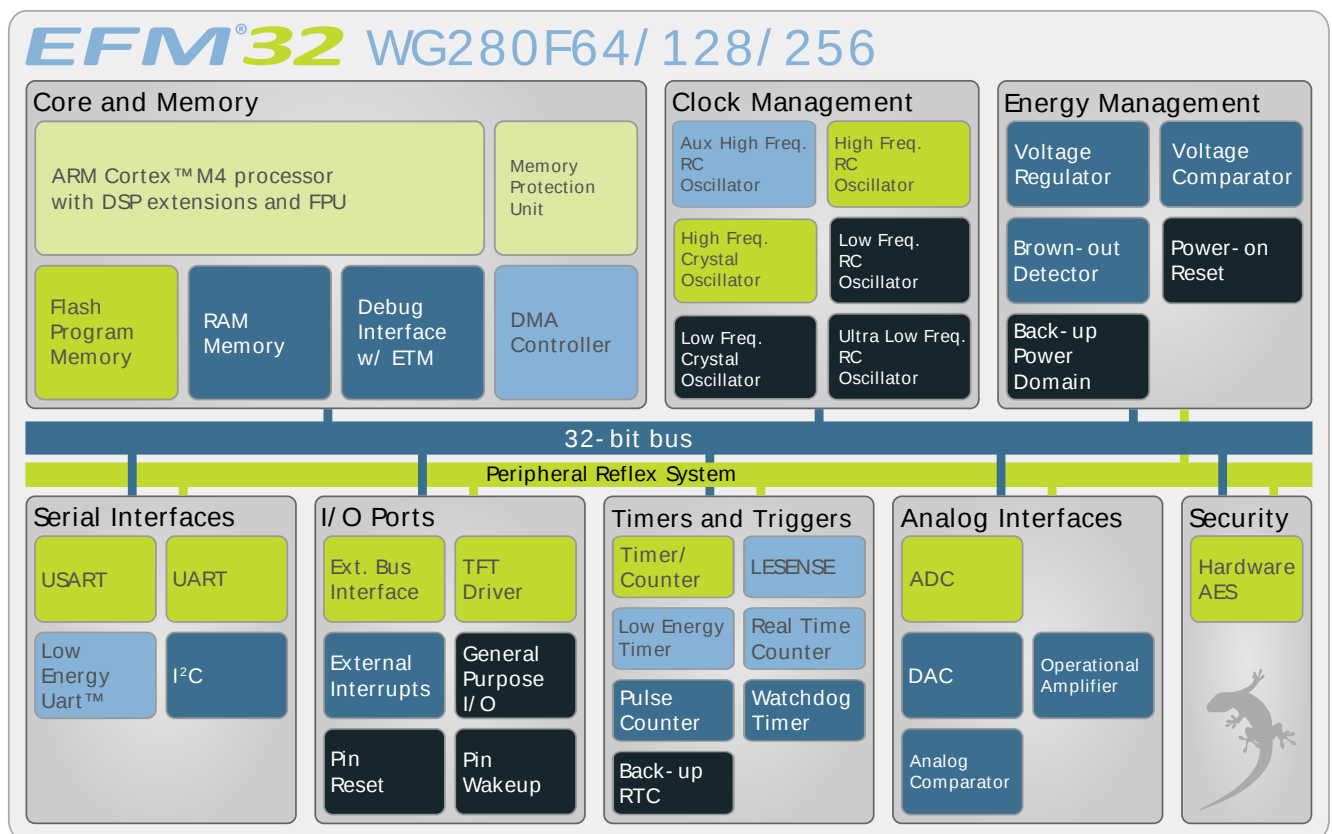
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M4, with DSP instruction support and floating-point unit, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32WG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32WG280 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32WG Reference Manual*.

A block diagram of the EFM32WG280 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M4 Core

The ARM Cortex-M4 includes a 32-bit RISC processor, with DSP instruction support and floating-point unit, which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M4 is described in detail in *ARM Cortex-M4 Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.27 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.28 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG280 to keep track of time and retain data, even if the main power source should drain out.

2.1.29 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.30 General Purpose Input/Output (GPIO)

In the EFM32WG280, there are 85 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32WG280 is a subset of the feature set described in the EFM32WG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M4	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1.2 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		271	286	$\mu\text{A}/\text{MHz}$
		1.2 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		275		$\mu\text{A}/\text{MHz}$
I_{EM1}	EM1 current (Production test condition = 14 MHz)	48 MHz HFXO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		63	75	$\mu\text{A}/\text{MHz}$
		48 MHz HFXO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		65	76	$\mu\text{A}/\text{MHz}$
		28 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		64	75	$\mu\text{A}/\text{MHz}$
		28 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		65	77	$\mu\text{A}/\text{MHz}$
		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		65	76	$\mu\text{A}/\text{MHz}$
		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		66	78	$\mu\text{A}/\text{MHz}$
		14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		67	79	$\mu\text{A}/\text{MHz}$
		14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		68	82	$\mu\text{A}/\text{MHz}$
		11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		68	81	$\mu\text{A}/\text{MHz}$
		11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		70	83	$\mu\text{A}/\text{MHz}$
		6.6 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		74	87	$\mu\text{A}/\text{MHz}$
		6.6 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		76	89	$\mu\text{A}/\text{MHz}$
		1.2 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		106	120	$\mu\text{A}/\text{MHz}$
		1.2 MHz HFRCO, all peripheral clocks disabled, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		112	129	$\mu\text{A}/\text{MHz}$
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		0.95 ¹	1.7 ¹	μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, $V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		3.0 ¹	4.0 ¹	μA
I_{EM3}	EM3 current	$V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		0.65	1.3	μA
		$V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		2.65	4.0	μA
I_{EM4}	EM4 current	$V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		0.02	0.055	μA
		$V_{DD}=3.0\text{ V}$, $T_{AMB}=85^{\circ}\text{C}$		0.44	0.9	μA

¹Using backup RTC.

3.4.1 EM1 Current Consumption

Figure 3.1. EM1 Current consumption with all peripheral clocks disabled and HFXO running at 48MHz

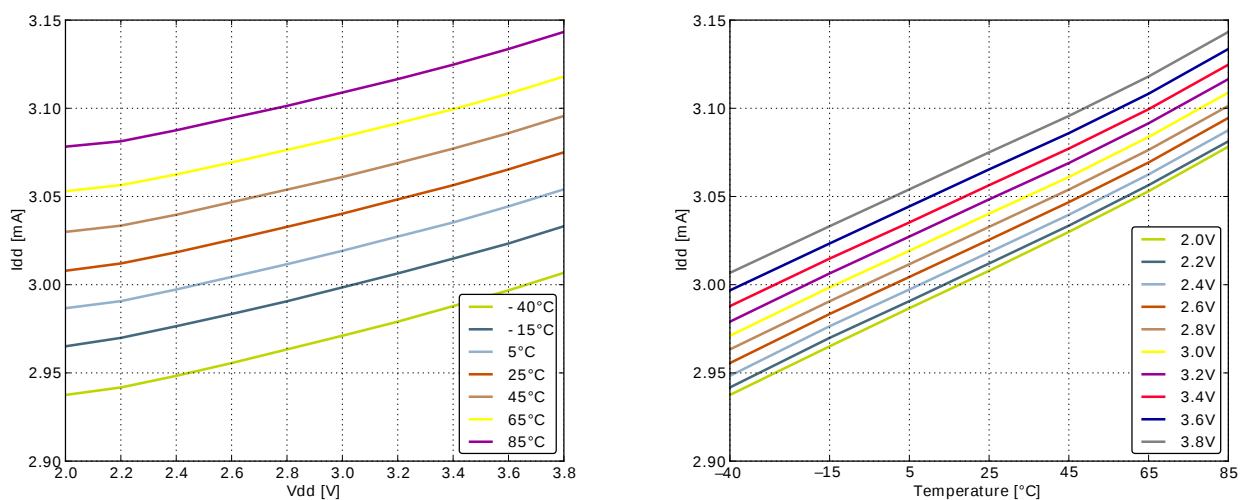
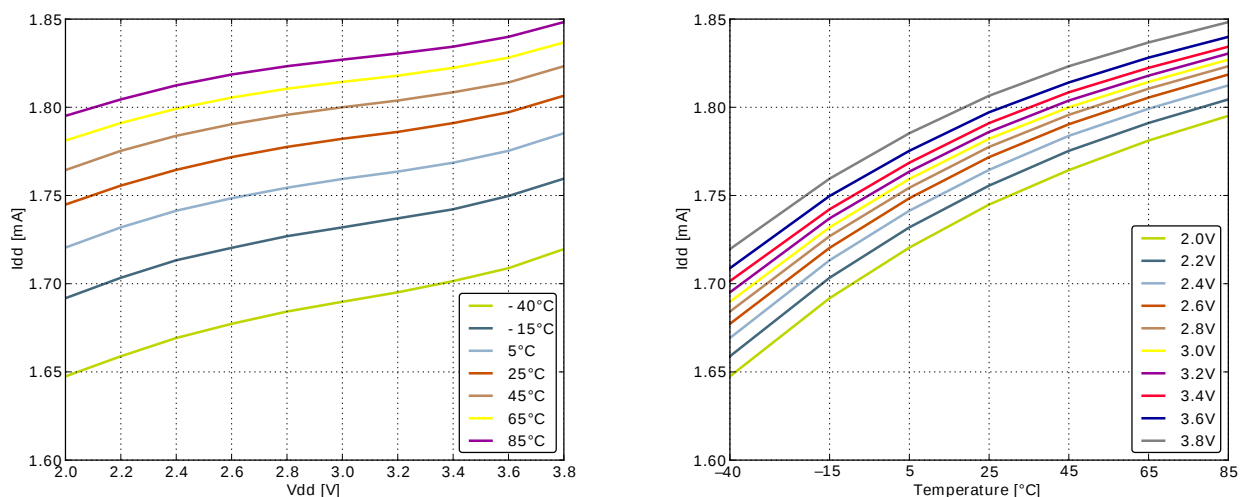


Figure 3.2. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28MHz



3.6 Power Management

The EFM32WG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage		1.74		1.96	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
RET _{FLASH}	Flash data retention	T _{AMB} <150°C	10000			h
		T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) programming time		20			μs
t _{PERASE}	Page erase time		20	20.4	20.8	ms
t _{DERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

¹Measured at 25°C

3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
		Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V

Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

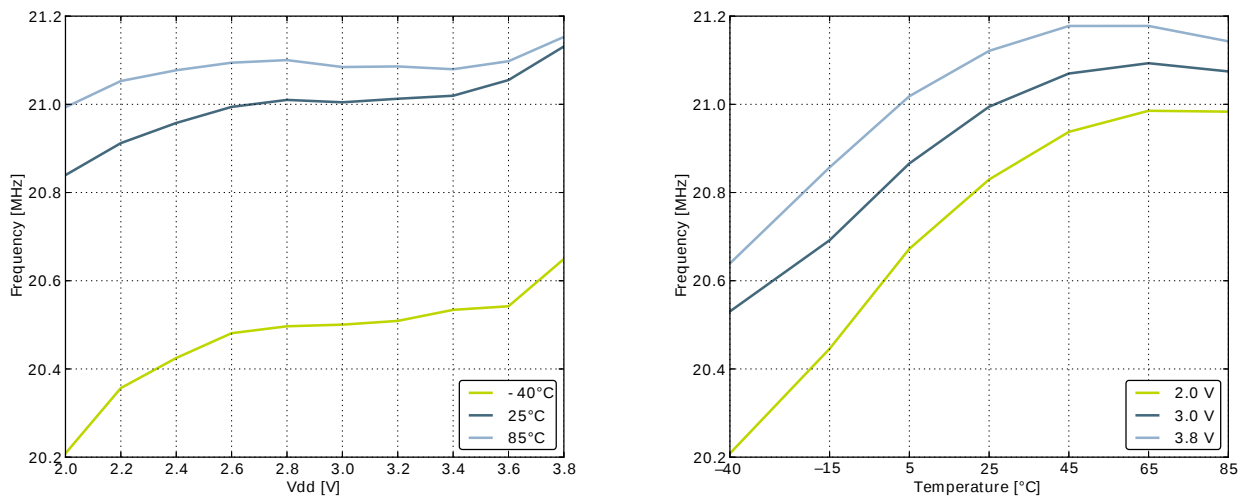
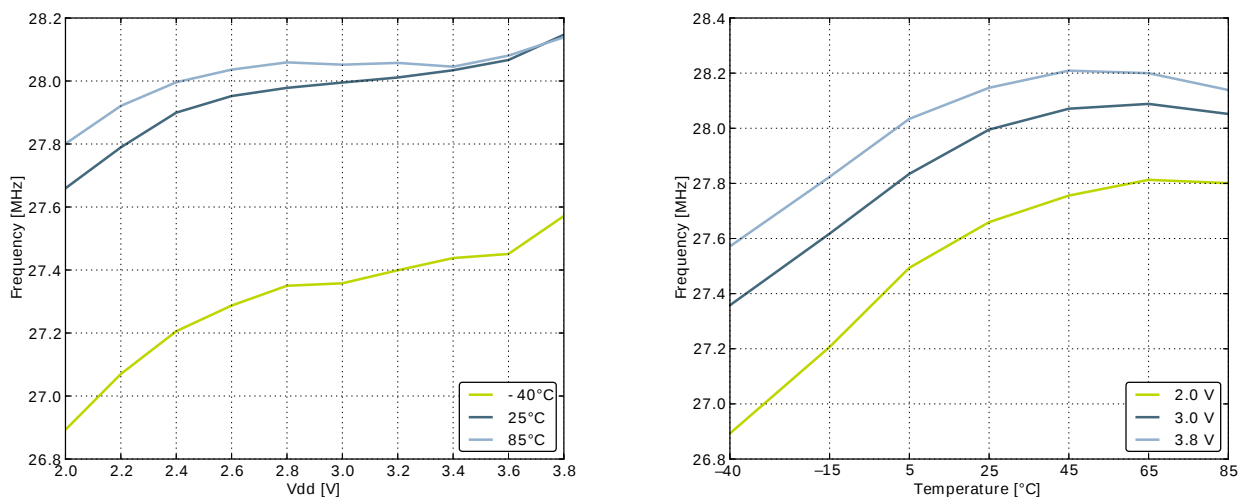


Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



Symbol	Parameter	Condition	Min	Typ	Max	Unit
	reference voltage on channel 6					
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
I _{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		μA
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MΩ
R _{ADCFLT}	Input RC filter resistance			10		kΩ
C _{ADCFLT}	Input RC filter/decoupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator			5		μs

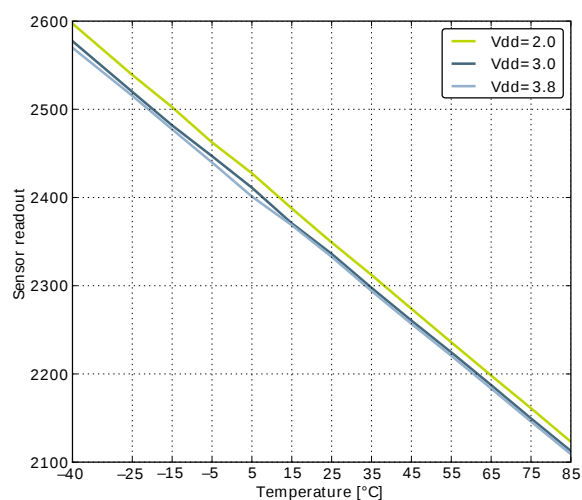
Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V _{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		79		dBc
V _{ADCOFFSET}	Offset voltage	After calibration, single ended	-3.5	0.3	3	mV
		After calibration, differential		0.3		mV
TGRAD _{ADCTH}	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL _{ADC}	Differential non-linearity (DNL)		-1	±0.7	4	LSB
INL _{ADC}	Integral non-linearity (INL), End point method			±1.2	±3	LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits
GAIN _{ED}	Gain error drift	1.25V reference		0.01 ²	0.033 ³	%/°C
		2.5V reference		0.01 ²	0.03 ³	%/°C
OFFSET _{ED}	Offset error drift	1.25V reference		0.2 ²	0.7 ³	LSB/°C
		2.5V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

²Typical numbers given by $\text{abs}(\text{Mean}) / (85 - 25)$.

³Max number given by $(\text{abs}(\text{Mean}) + 3 \times \text{stddev}) / (85 - 25)$.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.24 (p. 37) and Figure 3.25 (p. 37) , respectively.

Figure 3.31. ADC Temperature sensor readout

3.11 Digital Analog Converter (DAC)

Table 3.16. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400 ¹		μA
		100 kSamples/s, 12 bit		200 ¹		μA
		1 kSamples/s 12 bit NORMAL		17 ¹		μA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cycles per conversion			2		
$t_{DACCONV}$	Conversion time		2			μs
$t_{DACSETTLE}$	Settling time			5		μs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	25	μA
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C _L =75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V
		OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <V _{in} <V _{DD} , OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V _{SS} <V _{in} <V _{DD} -1.2, OPAxHCMDIS=1		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/μs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/μs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/μs
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}

3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

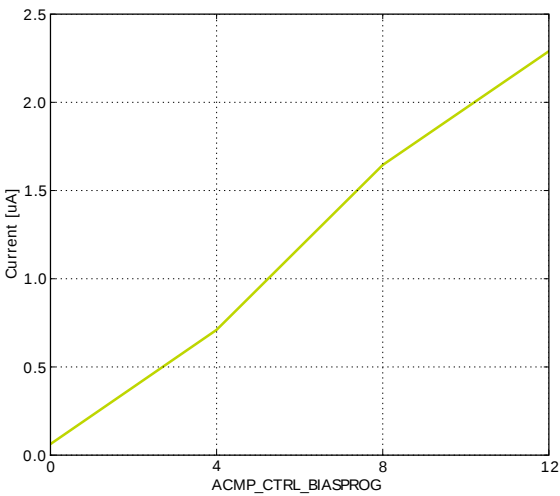
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULL-BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	μA
		BIASPROG=0b1111, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	μA
		BIASPROG=0b1111, FULL-BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	μA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μA
		Internal voltage reference		5		μA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

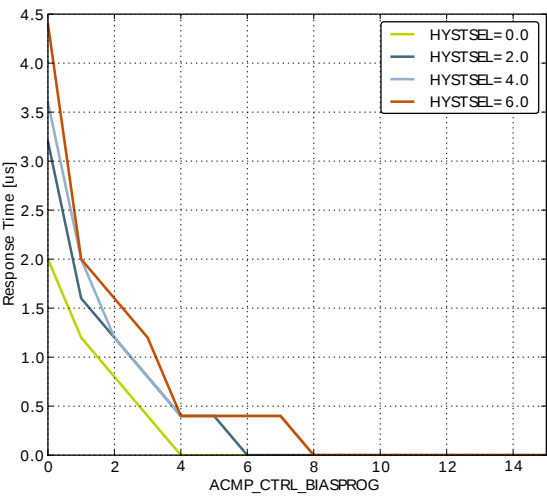
Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

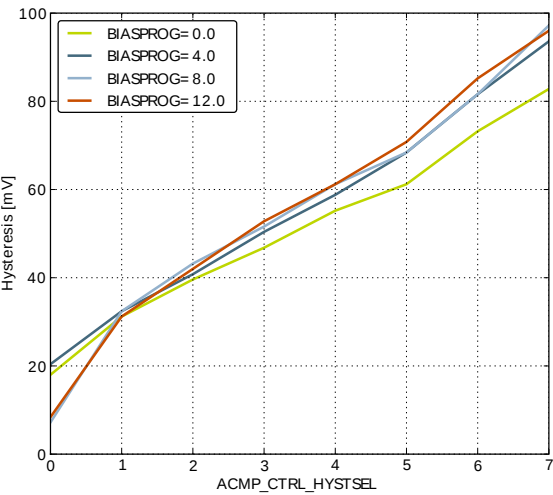
Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



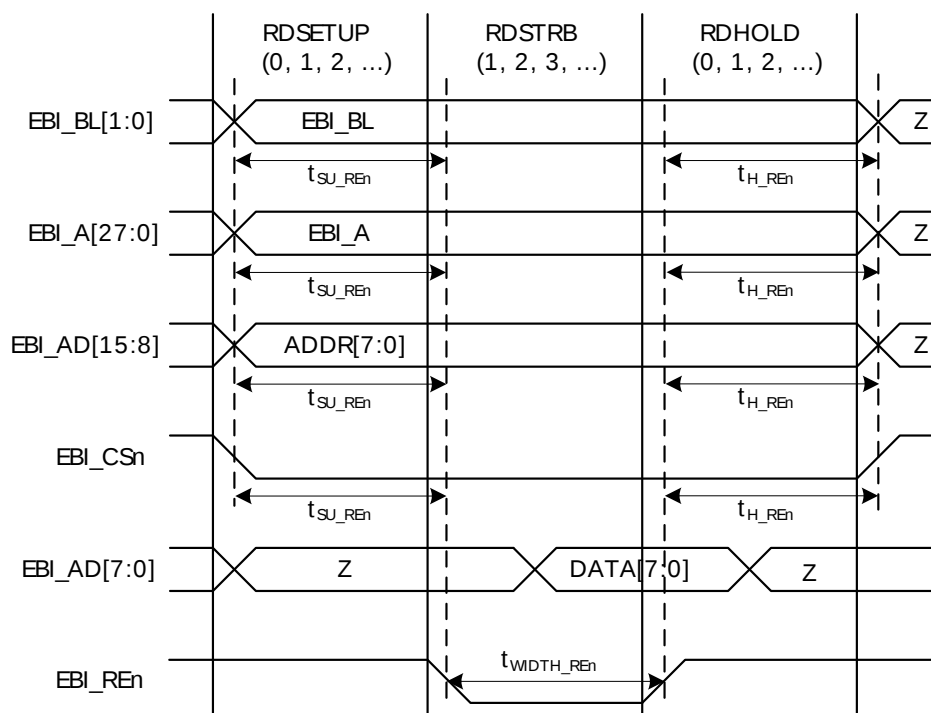
Current consumption, HYSTSEL = 4



Response time



Hysteresis

Figure 3.40. EBI Read Enable Related Output Timing**Table 3.22. EBI Read Enable Related Output Timing**

Symbol	Parameter	Min	Typ	Max	Unit
t _{OH_REn} ^{1 2 3 4}	Output hold time, from trailing EBI_REn/ EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CS, EBI_BLn invalid	-10.00 + (RDHOLD * t _{HFCORECLK})			ns
t _{OSU_REn} ^{1 2 3 4 5}	Output setup time, from EBI_AD, EBI_A, EBI_CS, EBI_BLn valid to leading EBI_REn/EBI_NANDREn edge	-10.00 + (RDSETUP * t _{HFCORECLK})			ns
t _{WIDTH_REn} ^{1 2 3 4 5 6}	EBI_REn pulse width	-9.00 + ((RD- STRB+1) * t _{HFCORE- CLK})			ns

¹Applies for all addressing modes (figure only shows D8A8. Output timing for EBI_AD only applies to multiplexed addressing modes D8A24ALE and D16A16ALE)

²Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * t_{HFCCLKNODIV}.

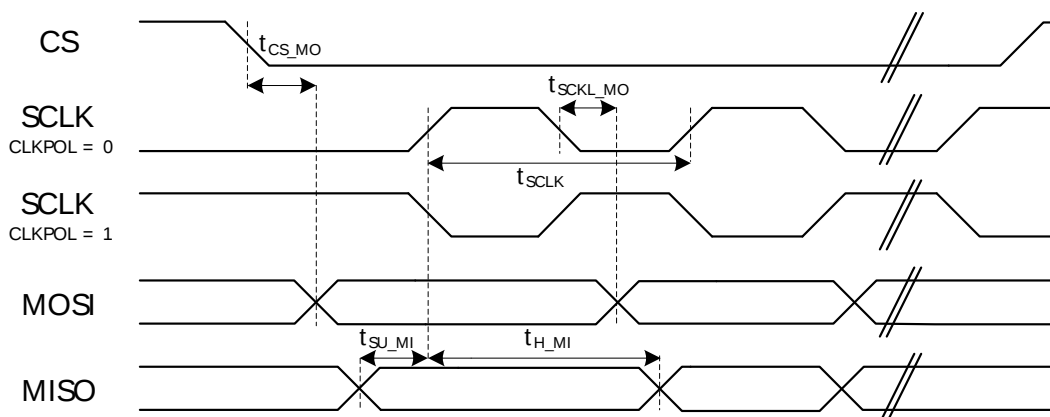
⁶When page mode is used, RDSTRB is replaced by RDPA for page hits.

Table 3.27. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000 ¹	kHz
t_{LOW}	SCL clock low time	0.5			μ s
t_{HIGH}	SCL clock high time	0.26			μ s
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			μ s
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			μ s
$t_{SU,STO}$	STOP condition set-up time	0.26			μ s
t_{BUF}	Bus free time between a STOP and a START condition	0.5			μ s

¹For the minimum HPPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32WG Reference Manual.

3.17 USART SPI

Figure 3.43. SPI Master Timing**Table 3.28. SPI Master Timing**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{SCLK}^{1,2}$	SCLK period		$2 * t_{HPPER-CLK}$			ns
$t_{CS_MO}^{1,2}$	CS to MOSI		-2.00		2.00	ns
$t_{SCLK_MO}^{1,2}$	SCLK to MOSI		-1.00		3.00	ns
$t_{SU_MI}^{1,2}$	MISO setup time	IOVDD = 3.0 V	36.00			ns
$t_{H_MI}^{1,2}$	MISO hold time		-6.00			ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

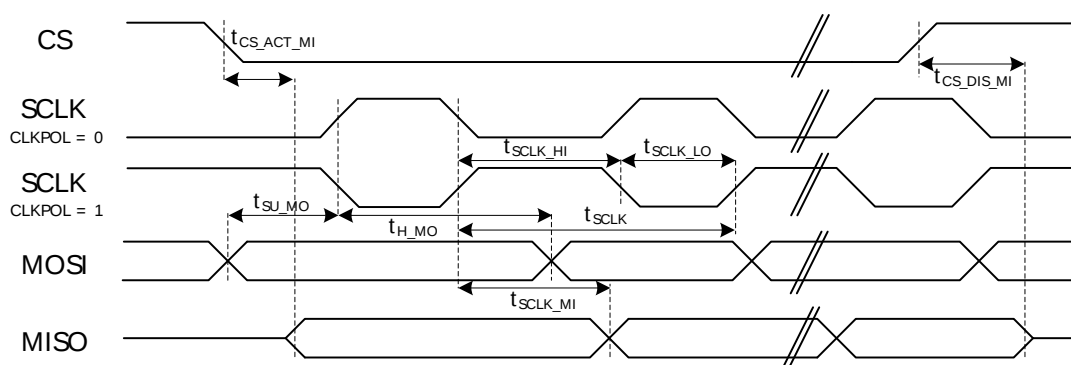
²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.29. SPI Master Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{\text{SCLK}}^{1,2}$	SCLK period		$2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_MO}}^{1,2}$	CS to MOSI		-2.00		2.00	ns
$t_{\text{SCLK_MO}}^{1,2}$	SCLK to MOSI		-1.00		3.00	ns
$t_{\text{SU_MI}}^{1,2}$	MISO setup time	IOVDD = 3.0 V	-32.00			ns
$t_{\text{H_MI}}^{1,2}$	MISO hold time		63.00			ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Figure 3.44. SPI Slave Timing**Table 3.30. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_sl}}^{1,2}$	SCKL period	$6 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_hi}}^{1,2}$	SCLK high period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_lo}}^{1,2}$	SCLK low period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_ACT_MI}}^{1,2}$	CS active to MISO	5.00		35.00	ns
$t_{\text{CS_DIS_MI}}^{1,2}$	CS disable to MISO	5.00		35.00	ns
$t_{\text{SU_MO}}^{1,2}$	MOSI setup time	5.00			ns
$t_{\text{H_MO}}^{1,2}$	MOSI hold time	$2 + 2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_MI}}^{1,2}$	SCLK to MISO	$7 + t_{\text{HFER-CLK}}$		$42 + 2 * t_{\text{HFERCLK}}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.31. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_sl}}^{1,2}$	SCKL period	$6 * t_{\text{HFER-CLK}}$			ns

Alternate	LOCATION							Description
Functionality	0	1	2	3	4	5	6	
EBI_AD09	PA0	PA0	PA0					External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	PA1	PA1	PA1					External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	PA2	PA2	PA2					External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	PA3	PA3	PA3					External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	PA4	PA4	PA4					External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	PA5	PA5	PA5					External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	PA6	PA6	PA6					External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	PF3	PC11	PC11					External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	PF2	PF2	PF2					External Bus Interface (EBI) Hardware Ready Control input.
EBI_BL0	PF6	PF6	PF6					External Bus Interface (EBI) Byte Lane/Enable pin 0.
EBI_BL1	PF7	PF7	PF7					External Bus Interface (EBI) Byte Lane/Enable pin 1.
EBI_CS0	PD9	PD9	PD9					External Bus Interface (EBI) Chip Select output 0.
EBI_CS1	PD10	PD10	PD10					External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	PD11	PD11	PD11					External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	PD12	PD12	PD12					External Bus Interface (EBI) Chip Select output 3.
EBI_CSTFT	PA7	PA7	PA7					External Bus Interface (EBI) Chip Select output TFT.
EBI_DCLK	PA8	PA8	PA8					External Bus Interface (EBI) TFT Dot Clock pin.
EBI_DTEN	PA9	PA9	PA9					External Bus Interface (EBI) TFT Data Enable pin.
EBI_HSNC	PA11	PA11	PA11					External Bus Interface (EBI) TFT Horizontal Synchronization pin.
EBI_NANDREn	PC3	PC3	PC3					External Bus Interface (EBI) NAND Read Enable output.
EBI_NANDWEn	PC5	PC5	PC5					External Bus Interface (EBI) NAND Write Enable output.
EBI_REn	PF5	PF9	PF5					External Bus Interface (EBI) Read Enable output.
EBI_VSNC	PA10	PA10	PA10					External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEn	PF4	PF8	PF4					External Bus Interface (EBI) Write Enable output.
ETM_TCLK	PD7	PF8	PC6	PA6				Embedded Trace Module ETM clock .
ETM_TD0	PD6	PF9	PC7	PA2				Embedded Trace Module ETM data 0.
ETM_TD1	PD3		PD3	PA3				Embedded Trace Module ETM data 1.
ETM_TD2	PD4		PD4	PA4				Embedded Trace Module ETM data 2.
ETM_TD3	PD5	PF3	PD5	PA5				Embedded Trace Module ETM data 3.
GPIO_EM4WU0	PA0							Pin can be used to wake the system up from EM4
GPIO_EM4WU1	PA6							Pin can be used to wake the system up from EM4
GPIO_EM4WU2	PC9							Pin can be used to wake the system up from EM4
GPIO_EM4WU3	PF1							Pin can be used to wake the system up from EM4
GPIO_EM4WU4	PF2							Pin can be used to wake the system up from EM4
GPIO_EM4WU5	PE13							Pin can be used to wake the system up from EM4
HFX TAL_N	PB14							High Frequency Crystal negative pin. Also used as external optional clock input pin.

Table 4.4. LQFP100 (Dimensions in mm)

		SYMBOL	MIN	NOM	MAX
total thickness		A	--	--	1.6
stand off		A1	0.05	--	0.15
mold thickness		A2	1.35	1.4	1.45
lead width (plating)		b	0.17	0.2	0.27
lead width		b1	0.17	--	0.23
L/F thickness (plating)		c	0.09	--	0.2
lead thickness		c1	0.09	--	0.16
body size	x	D	16 BSC		
	y	E	16 BSC		
	x	D1	14 BSC		
	y	E1	14 BSC		
lead pitch		e	0.5 BSC		
		L	0.45	0.6	0.75
footprint		L1	1 REF		
		θ	0°	3.5°	7°
		θ1	0°	--	--
		θ2	11°	12°	13°
		θ3	11°	12°	13°
		R1	0.08	--	--
		R1	0.08	--	0.2
		S	0.2	--	--
package edge tolerance		aaa	0.2		
lead edge tolerance		bbb	0.2		
coplanarity		ccc	0.08		
lead offset		ddd	0.08		
mold flatness		eee	0.05		

The LQFP100 Package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:

<http://www.silabs.com/support/quality/pages/default.aspx>

Updated the EM0 and EM1 current consumption numbers. Updated the the EM1 plots and removed the EM0 plots.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.4 Revision 1.20

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.5 Revision 1.10

May 6th, 2013

Updated current consumption table and figures in Electrical characteristics section.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.95

May 3rd, 2012

Updated EM2/EM3 current consumption at 85°C.

7.8 Revision 0.90

February 27th, 2012

Initial preliminary release.

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